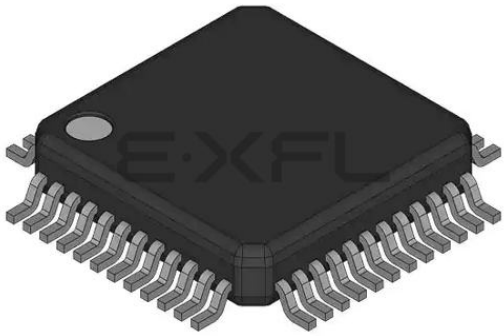

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- Package options
  - 64-pin LQFP; 64-pin QFP
  - 48-pin LQFP
  - 44-pin LQFP
  - 32-pin LQFP

Table of Contents

Field	Description	Values
B	Operating temperature range (°C)	• V = –40 to 105
CC	Package designator	• QH = 64-pin QFP • LH = 64-pin LQFP • LF = 48-pin LQFP • LD = 44-pin LQFP • LC = 32-pin LQFP

2.4 Example

This is an example part number:

MC9S08PT60VQH

3 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 1. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-6000	+6000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in below table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this document.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Symbol	Description	Min.	Max.	Unit
V_{DD}	Supply voltage	–0.3	6.0	V
I_{DD}	Maximum current into V_{DD}	—	120	mA
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, XTAL, or true open drain pin PTA2 and PTA3)	–0.3	V_{DD} + 0.3	V
	Digital input voltage (true open drain pin PTA2 and PTA3)	-0.3	6	V
V_{AIO}	Analog[1], $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

1. All digital I/O pins, except open-drain pin PTA2 and PTA3, are internally clamped to V_{SS} and V_{DD}. PTA2 and PTA3 is only clamped to V_{SS}.

5 General

5.1 Nonswitching electrical specifications

5.1.1 DC characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 2. DC characteristics

Symbol	C	Descriptions			Min	Typical[1]	Max	Unit
—	—	Operating voltage		—	2.7	—	5.5	V
V_{OH}	P	Output high voltage	All I/O pins, standard-drive strength	5 V, I_{load} = -5 mA	V_{DD} - 0.8	—	—	V
	C			3 V, I_{load} = -2.5 mA	V_{DD} - 0.8	—	—	V
	P		High current drive pins, high-drive strength[2]	5 V, I_{load} = -20 mA	V_{DD} - 0.8	—	—	V
	C			3 V, I_{load} = -10 mA	V_{DD} - 0.8	—	—	V

Table continues on the next page...

Table 4. Supply current characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V_{DD} (V)	Typical[1]	Max	Unit	Temp
	C	ADLPC = 1 ADLSMP = 1 ADCO = 1 MODE = 10B ADICLK = 11B			3	40	—		
8	C	TSI adder to stop3[4]	—	—	5	111	—	µA	-40 to 105 °C
	C	PS = 010B NSCN =0x0F EXTCHRG = 0 REFCHRG = 0 DVOLT = 01B			3	110	—		
9	C	LVD adder to stop3[5]	—	—	5	130	—	µA	-40 to 105 °C
	C				3	125	—		

1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
2. RTC adder cause <1 µA I_{DD} increase typically, RTC clock source is 1 kHz LPO clock.
3. ACMP adder cause <10 µA I_{DD} increase typically.
4. The current varies with TSI configuration and capacity of touch electrode. Please refer to TSI electrical specifications.
5. LVD is periodically woken up from stop3 by 5% duty cycle. The period is equal to or less than 2 ms.

5.1.3 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

5.1.3.1 EMC radiated emissions operating behaviors

Table 5. EMC radiated emissions operating behaviors for 64-pin SOIC package

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	12	dBµV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	10	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	4	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	5	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	N	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 5.0 V, T_A = 25 °C, f_{OSC} = 10 MHz (crystal), f_{SYS} = 20 MHz, f_{BUS} = 20 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2 Switching specifications

5.2.1 Control timing

Table 6. Control timing

Num	C	Rating		Symbol	Min	Typical[1]	Max	Unit
1	P	Bus frequency (t_{cyc} = 1/f_{Bus})		f_{Bus}	DC	—	20	MHz
2	P	Internal low power oscillator frequency		f_{LPO}	0.67	1.0	1.25	KHz
3	D	External reset pulse width[2]		t_{extrst}	1.5 × t_{cyc}	—	—	ns
4	D	Reset low drive		t_{rstdrv}	34 × t_{cyc}	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes		t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes[3]		t_{MSH}	100	—	—	ns
7	D	IRQ pulse width	Asynchronous path[2]	t_{ILIH}	100	—	—	ns
	D		Synchronous path[4]	t_{IHIL}	1.5 × t_{cyc}	—	—	ns
8	D	Keyboard interrupt pulse width	Asynchronous path[2]	t_{ILIH}	100	—	—	ns
	D		Synchronous path	t_{IHIL}	1.5 × t_{cyc}	—	—	ns
9	C	Port rise and fall time - standard drive strength (load = 50 pF)[5]	—	t_{Rise}	—	10.2	—	ns
	C			t_{Fall}	—	9.5	—	ns
	C	Port rise and fall time - high drive strength (load = 50 pF)[5]	—	t_{Rise}	—	5.4	—	ns
	C			t_{Fall}	—	4.6	—	ns

1. Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.
2. This is the shortest pulse that is guaranteed to be recognized as a reset pin request.
3. To enter BDM mode following a POR, BKGD/MS must be held low during the powerup and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.
4. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.
5. Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels in operating temperature range.

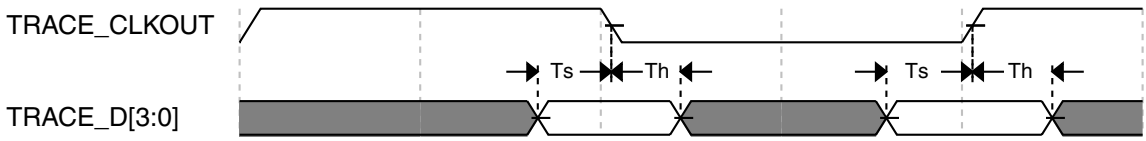


Figure 12. Trace data specifications

5.2.3 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 8. FTM input timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

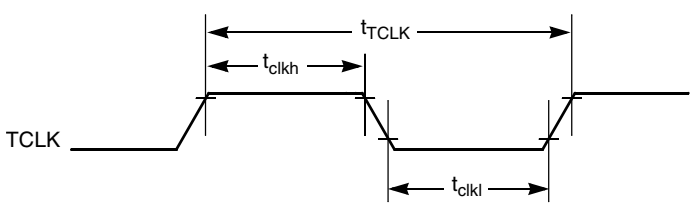


Figure 13. Timer external clock

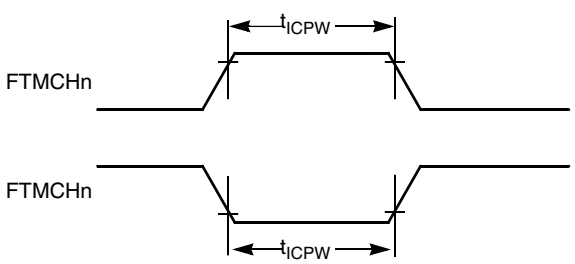


Figure 14. Timer input capture pulse

5.3 Thermal specifications

5.3.1 Thermal operating requirements

Table 9. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

NOTE

Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

5.3.2 Thermal characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 10. Thermal attributes

Board type	Symbol	Description	64 LQFP	64 QFP	48 LQFP	44 LQFP	32 LQFP	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	71	61	81	75	86	°C/W	1, 2
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	53	47	57	53	57	°C/W	1, 3
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	59	50	68	62	72	°C/W	1, 3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	46	41	50	47	51	°C/W	1, 3

Table continues on the next page...

Table 10. Thermal attributes (continued)

Board type	Symbol	Description	64 LQFP	64 QFP	48 LQFP	44 LQFP	32 LQFP	Unit	Notes
—	$R_{\theta JB}$	Thermal resistance, junction to board	35	32	34	34	33	°C/W	4
—	$R_{\theta JC}$	Thermal resistance, junction to case	20	23	24	20	24	°C/W	5
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	5	8	6	5	6	°C/W	6

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board (JESD51-3) horizontal.
3. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the solder pad on the bottom of the package. Interface resistance is ignored.
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization.

6 Peripheral operating requirements and behaviors

6.1 External oscillator (XOSC) and ICS characteristics

Table 11. XOSC and ICS specifications (temperature range = -40 to 105 °C ambient)

Num	C	Characteristic		Symbol	Min	Typical[1]	Max	Unit
1	C	Oscillator crystal or resonator	Low range (RANGE = 0)	f_{lo}	31.25	32.768	39.0625	kHz
	C		High range (RANGE = 1) FEE or FBE mode[2]	f_{hi}	4	—	20	MHz
	C		High range (RANGE = 1), high gain (HGO = 1), FBELP mode	f_{hi}	4	—	20	MHz
	C		High range (RANGE = 1), low power (HGO = 0), FBELP mode	f_{hi}	4	—	20	MHz
2	D	Load capacitors		C1, C2	See Note[3]			
3	D	Feedback resistor	Low Frequency, Low-Power Mode[4]	R_F	—	—	—	MΩ
			Low Frequency, High-Gain Mode		—	10	—	MΩ
			High Frequency, Low-Power Mode		—	1	—	MΩ

Table continues on the next page...

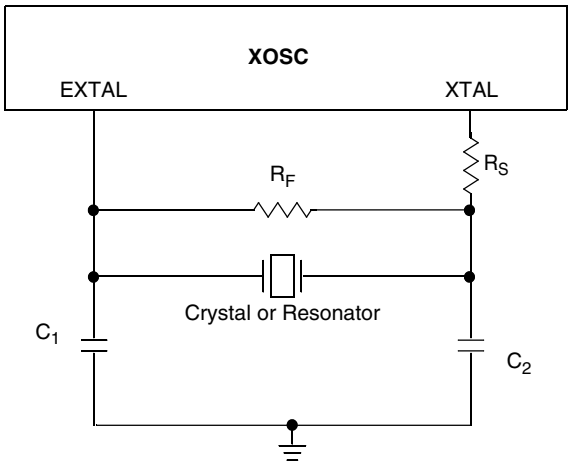


Figure 15. Typical crystal or resonator circuit

6.2 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

Table 12. Flash characteristics

C	Characteristic	Symbol	Min[1]	Typical[2]	Max[3]	Unit[4]
D	Supply voltage for program/erase -40 °C to 105 °C	$V_{prog/erase}$	2.7	—	5.5	V
D	Supply voltage for read operation	V_{Read}	2.7	—	5.5	V
D	NVM Bus frequency	f_{NVMBUS}	1	—	25	MHz
D	NVM Operating frequency	f_{NVMOP}	0.8	1	1.05	MHz
D	Erase Verify All Blocks	t_{VFYALL}	—	—	17338	t_{cyc}
D	Erase Verify Flash Block	t_{RD1BLK}	—	—	16913	t_{cyc}
D	Erase Verify EEPROM Block	t_{RD1BLK}	—	—	810	t_{cyc}
D	Erase Verify Flash Section	t_{RD1SEC}	—	—	484	t_{cyc}
D	Erase Verify EEPROM Section	$t_{DRD1SEC}$	—	—	555	t_{cyc}
D	Read Once	t_{RDONCE}	—	—	450	t_{cyc}
D	Program Flash (2 word)	t_{PGM2}	0.12	0.12	0.29	ms
D	Program Flash (4 word)	t_{PGM4}	0.20	0.21	0.46	ms
D	Program Once	$t_{PGMONCE}$	0.20	0.21	0.21	ms
D	Program EEPROM (1 Byte)	t_{DPGM1}	0.10	0.10	0.27	ms
D	Program EEPROM (2 Byte)	t_{DPGM2}	0.17	0.18	0.43	ms
D	Program EEPROM (3 Byte)	t_{DPGM3}	0.25	0.26	0.60	ms
D	Program EEPROM (4 Byte)	t_{DPGM4}	0.32	0.33	0.77	ms
D	Erase All Blocks	t_{ERSALL}	96.01	100.78	101.49	ms
D	Erase Flash Block	t_{ERSBLK}	95.98	100.75	101.44	ms

Table continues on the next page...

Table 13. 5 V 12-bit ADC operating conditions (continued)

Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
	10-bit mode • f_{ADCK} > 4 MHz • f_{ADCK} < 4 MHz		— —	— —	5 10		
	8-bit mode (all valid f_{ADCK})		—	—	10		
ADC conversion clock frequency	High speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	—
	Low power (ADLPC=1)		0.4	—	4.0		

1. Typical values assume V_{DDA} = 5.0 V, Temp = 25°C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.

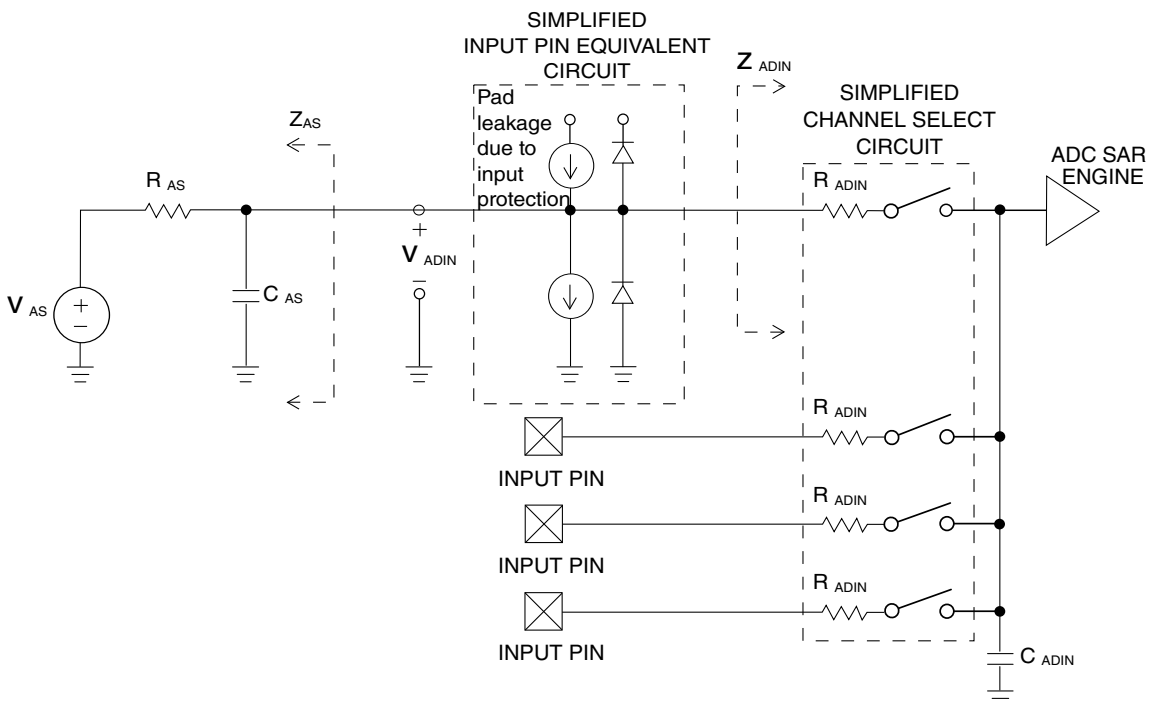
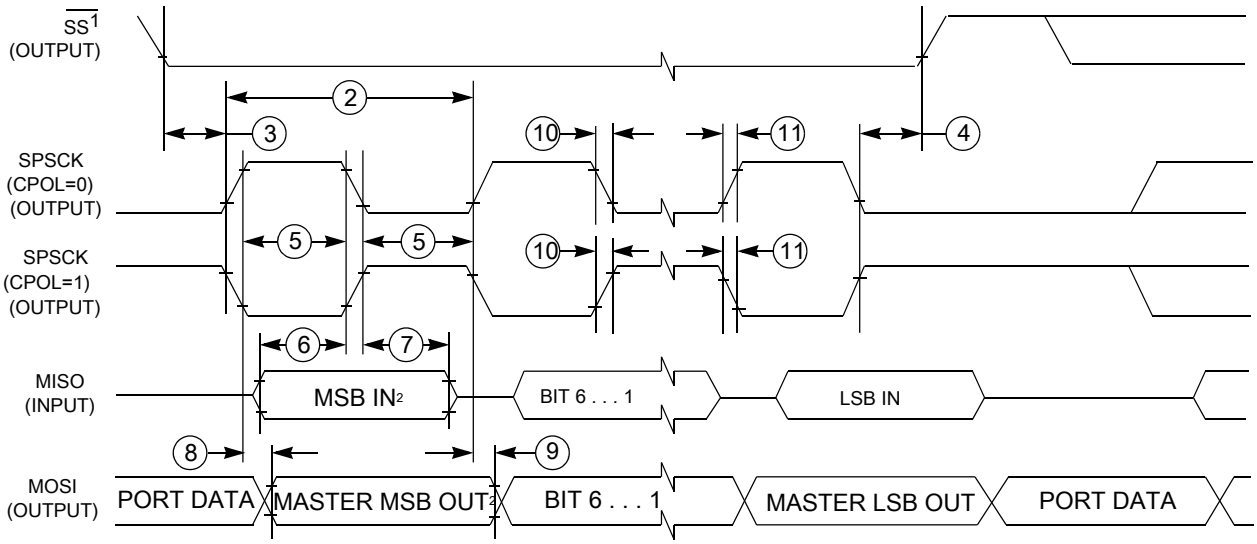


Figure 16. ADC input impedance equivalency diagram

Table 14. 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit
Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		T	I_{DDA}	—	133	—	µA
Supply current		T	I_{DDA}	—	218	—	µA

Table continues on the next page...



1.If configured as output

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 18. SPI master mode timing (CPHA=1)

Table 17. SPI slave mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	0	$f_{Bus}/4$	Hz	f_{Bus} is the bus clock as defined in .
2	t_{SPSCK}	SPSCK period	4 x t_{Bus}	—	ns	$t_{Bus} = 1/f_{Bus}$
3	t_{Lead}	Enable lead time	1	—	t_{Bus}	—
4	t_{Lag}	Enable lag time	1	—	t_{Bus}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{Bus} - 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	15	—	ns	—
7	t_{HI}	Data hold time (inputs)	25	—	ns	—
8	t_a	Slave access time	—	t_{Bus}	ns	Time to data active from high-impedance state
9	t_{dis}	Slave MISO disable time	—	t_{Bus}	ns	Hold time to high-impedance state
10	t_v	Data valid (after SPSCK edge)	—	25	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{Bus} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

6.5.1 TSI electrical specifications

Table 18. TSI electrical specifications

Symbol	Description	Min.	Type	Max	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	µA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	—	128	µA
TSI_EN	Power consumption in enable mode	—	100	—	µA
TSI_DIS	Power consumption in disable mode	—	1.2	—	µA
TSI_TEN	TSI analog enable time	—	66	—	µs
TSI_CREF	TSI reference capacitor	—	1.0	—	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	-10	—	10	%

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin LQFP	98ASH70029A
44-pin LQFP	98ASS23225W
48-pin LQFP	98ASH00962A
64-pin QFP	98ASB42844B
64-pin LQFP	98ASS23234W

8 Pinout

8.1 Signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

Table 19. Pin availability by package pin-count

Pin Number				Lowest Priority <-- --> Highest				
64-LQFP 64-QFP	48-LQFP	44-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	1	1	1	PTD1[1]	KBI1P1	FTM2CH3	MOSI1	—
2	2	2	2	PTD0[1]	KBI1P0	FTM2CH2	SPSCK1	—
3	—	—	—	PTH7	—	—	—	—
4	—	—	—	PTH6	—	—	—	—
5	3	3	—	PTE7	—	TCLK2	—	—
6	4	4	—	PTH2	—	BUSOUT	—	—
7	5	5	3	—	—	—	—	V_{DD}
8	6	6	4	—	—	—	V_{DDA}	V_{REFH}
9	7	7	5	—	—	—	V_{SSA}	V_{REFL}
10	8	8	6	—	—	—	—	V_{SS}
11	9	9	7	PTB7	—	SCL	—	EXTAL
12	10	10	8	PTB6	—	SDA	—	XTAL
13	11	11	—	—	—	—	—	V_{SS}
14	—	—	—	PTH1[1]	—	FTM2CH1	—	—
15	—	—	—	PTH0[1]	—	FTM2CH0	—	—
16	12	—	—	PTE6	—	—	—	—
17	13	—	—	PTE5	—	—	—	—
18	14	12	9	PTB5[1]	FTM2CH5	$\overline{SS0}$	—	—
19	15	13	10	PTB4[1]	FTM2CH4	MISO0	—	—
20	16	14	11	PTC3	FTM2CH3	—	ADP11	—
21	17	15	12	PTC2	FTM2CH2	—	ADP10	—
22	18	16	—	PTD7	KBI1P7	TXD2	—	—
23	19	17	—	PTD6	KBI1P6	RXD2	—	—
24	20	18	—	PTD5	KBI1P5	—	—	—
25	21	19	13	PTC1	—	FTM2CH1	ADP9	TSI7
26	22	20	14	PTC0	—	FTM2CH0	ADP8	TSI6
27	—	—	—	PTF7	—	—	ADP15	—
28	—	—	—	PTF6	—	—	ADP14	—
29	—	—	—	PTF5	—	—	ADP13	—
30	—	—	—	PTF4	—	—	ADP12	—
31	23	21	15	PTB3	KBI0P7	MOSI0	ADP7	TSI5
32	24	22	16	PTB2	KBI0P6	SPSCK0	ADP6	TSI4
33	25	23	17	PTB1	KBI0P5	TXD0	ADP5	TSI3
34	26	24	18	PTB0	KBI0P4	RXD0	ADP4	TSI2
35	—	—	—	PTF3	—	—	—	TSI15
36	—	—	—	PTF2	—	—	—	TSI14
37	27	25	19	PTA7	FTM2FAULT2	—	ADP3	TSI1

Table continues on the next page...

Table 19. Pin availability by package pin-count (continued)

Pin Number				Lowest Priority <-- --> Highest				
64-LQFP 64-QFP	48-LQFP	44-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
38	28	26	20	PTA6	FTM2FAULT1	—	ADP2	TSI0
39	29	—	—	PTE4	—	—	—	—
40	30	27	—	—	—	—	—	V_{SS}
41	31	28	—	—	—	—	—	V_{DD}
42	—	—	—	PTF1	—	—	—	TSI13
43	—	—	—	PTF0	—	—	—	TSI12
44	32	29	—	PTD4	KBI1P4	—	—	—
45	33	30	21	PTD3	KBI1P3	$\overline{SS1}$	—	TSI11
46	34	31	22	PTD2	KBI1P2	MISO1	—	TSI10
47	35	32	23	PTA3[2]	KBI0P3	TXD0	SCL	—
48	36	33	24	PTA2[2]	KBI0P2	RXD0	SDA	—
49	37	34	25	PTA1	KBI0P1	FTM0CH1	ACMP1	ADP1
50	38	35	26	PTA0	KBI0P0	FTM0CH0	ACMP0	ADP0
51	39	36	27	PTC7	—	TxD1	—	TSI9
52	40	37	28	PTC6	—	RxD1	—	TSI8
53	41	—	—	PTE3	—	$\overline{SS0}$	—	—
54	42	38	—	PTE2	—	MISO0	—	—
55	—	—	—	PTG3	—	—	—	—
56	—	—	—	PTG2	—	—	—	—
57	—	—	—	PTG1	—	—	—	—
58	—	—	—	PTG0	—	—	—	—
59	43	39	—	PTE1[1]	—	MOSI0	—	—
60	44	40	—	PTE0[1]	—	SPSCK0	TCLK1	—
61	45	41	29	PTC5	—	FTM1CH1	—	—
62	46	42	30	PTC4	—	FTM1CH0	RTCO	—
63	47	43	31	PTA5	IRQ	TCLK0	—	$\overline{RESET}$
64	48	44	32	PTA4	—	ACMPO	BKGD	MS

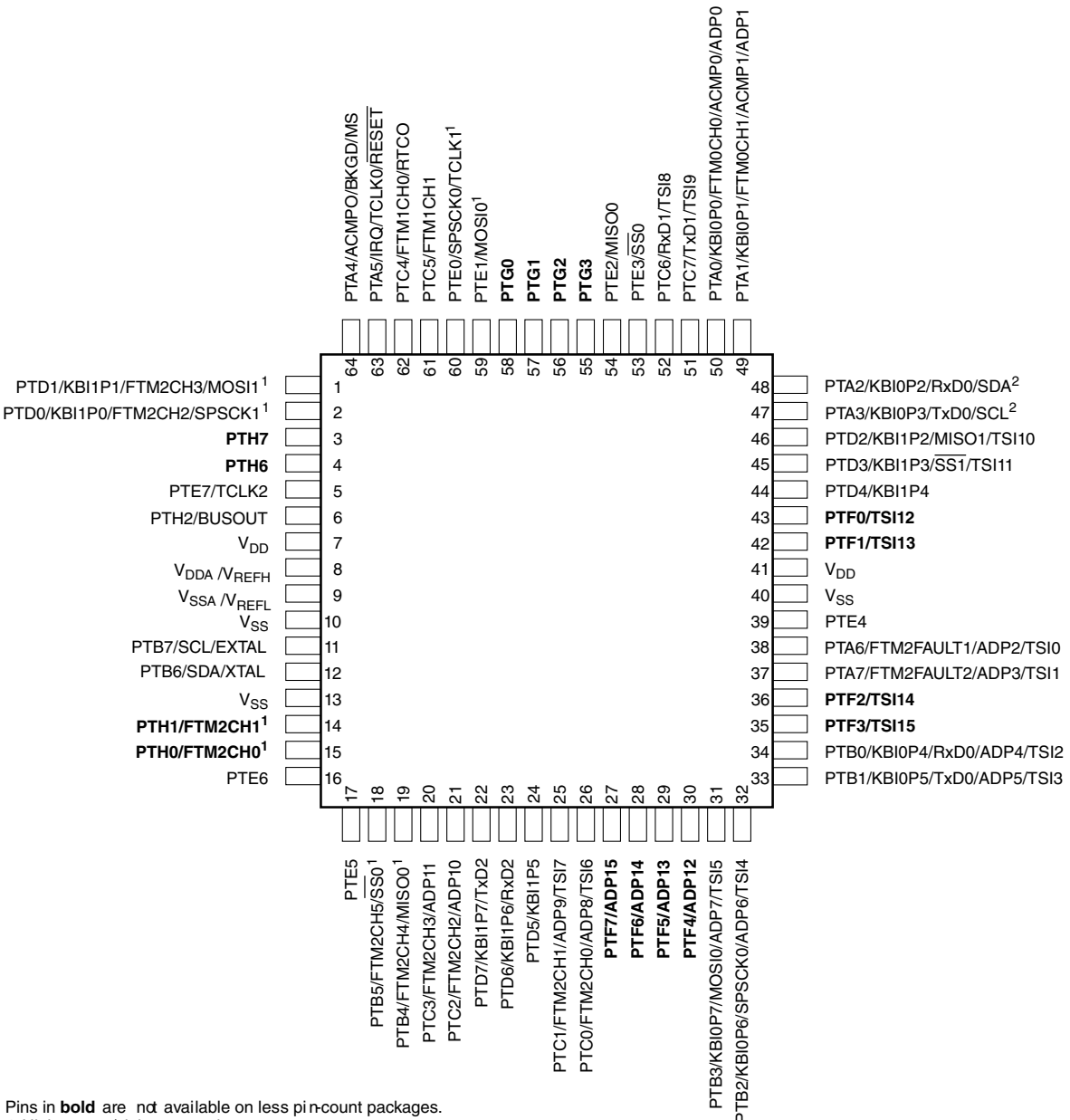
1. This is a high current drive pin when operated as output.
2. This is a true open-drain pin when operated as output.

Note

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear any associated flags before interrupts are enabled. The table above illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function

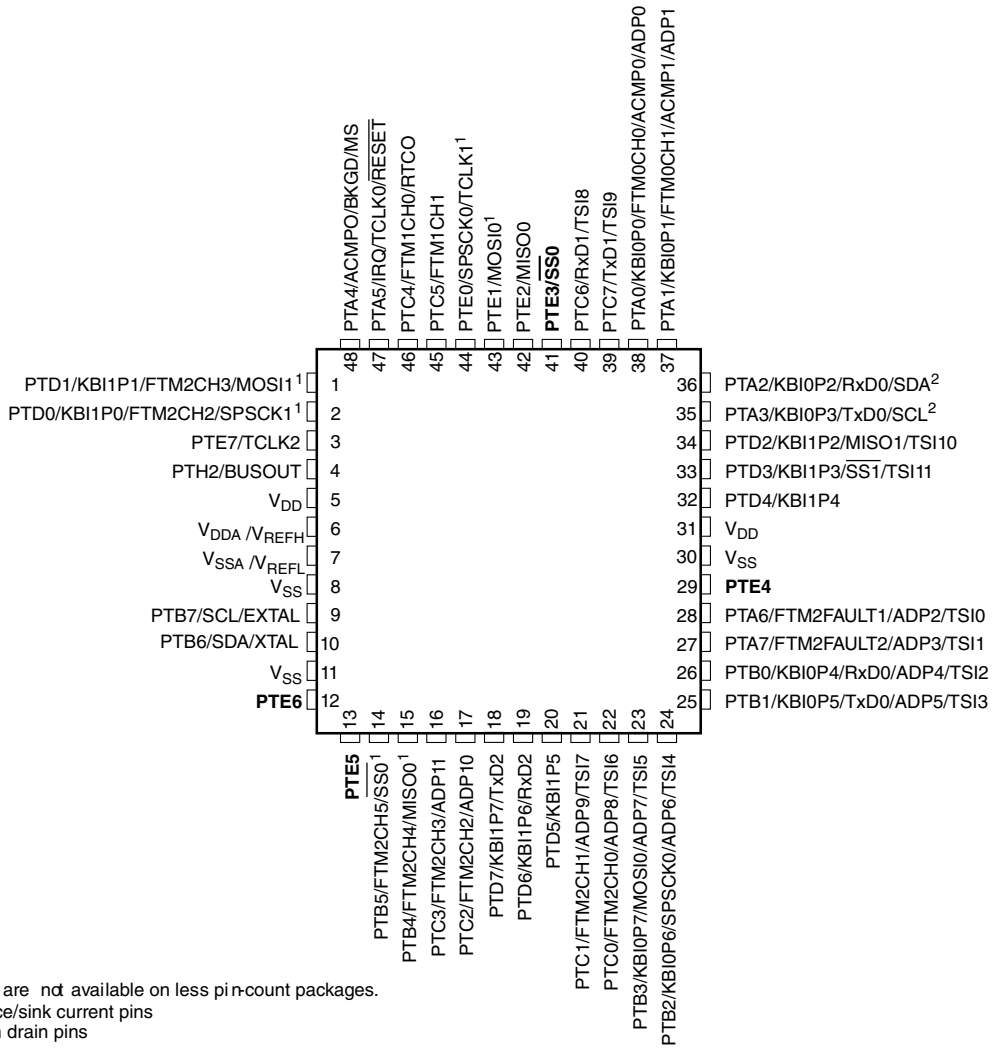
already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.

8.2 Device pin assignment



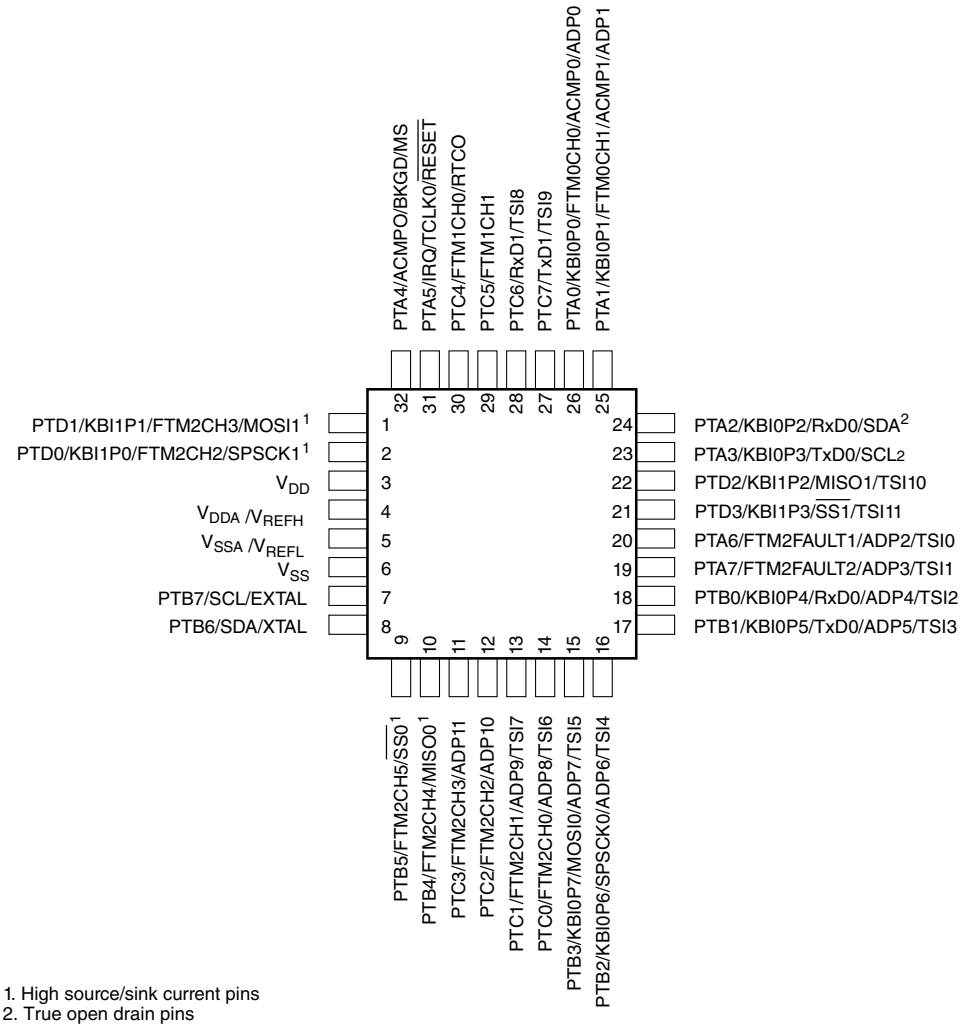
Pins in **bold** are not available on less pin-count packages.
1. High source/sink current pins
2. True open drain pins

Figure 21. MC9S08PT60 64-pin QFP and LQFP package



Pins in **bold** are not available on less pin-count packages.
1. High source/sink current pins
2. True open drain pins

Figure 22. MC9S08PT60 48-pin LQFP package



1. High source/sink current pins
2. True open drain pins

Figure 24. MC9S08PT60 32-pin LQFP package

9 Revision history

The following table provides a revision history for this document.

Table 20. Revision history

Rev. No.	Date	Substantial Changes
1	10/2011	Initial public revision.
2	11/2011	• Updated some TBDs • Updated LVD and POR data • Updated ADC data • Updated SPI data • Updated TSI data.
3	4/2012	• Finished all the TBDs • Updated package information
4	09/2014	• Updated V_{HBM} in ESD handling ratings

Table continues on the next page...

Table 20. Revision history (continued)

Rev. No.	Date	Substantial Changes
		• Updated V_{DD} and V_{DIO} in Voltage and current operating ratings • Updated the specs and figures in DC characteristics • Updated Thermal characteristics • Updated f_{lo} and the footnote to the $t_{Acquire}$ in External oscillator (XOSC) and ICS characteristics • Updated footnote on the $S3I_{DD}$ in Supply current characteristics • Updated flash characteristics in NVM specifications • Added EMC radiated emissions operating behaviors • Updated V_{OH} and V_{OL} in DC characteristics • Updated the rating descriptions for t_{Rise} and t_{Fall} in Control timing • Updated the assumption for all the timing values in SPI switching specifications • Updated the part number format to add new field for new part numbers in Fields.
5	06/2015	• Corrected the Min. of the t_{extrst} in Control timing • Added new section of Thermal operating requirements, Updated Thermal characteristics to remove redundant information.